SHI LING® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

Specifcation of products

：

：MURP200400CT

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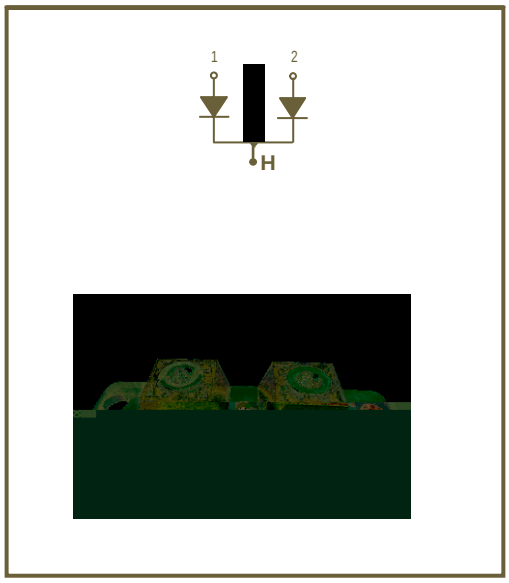
Equivalent

Equivalent Circuit



Thermal Characteristics

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance	Junction to Case	-	-	0.15	℃/W

Electrical Characteristics @ T_j=25℃(unless otherwise specified)

Symbol	Parameter	Conditions		Values			Unit
				Min.	Typ.	Max.	
V_R	Cathode Anode Breakdown Voltage	I_R= 100uA		400	-	-	V
V_{FM}	Maximum Forward Voltage	I_{FM}= 200A, T_c= 25℃		-	1.0	1.1	V
		I_{FM}= 200A, T_c =100℃		-	0.9	1.0	V
I_{RRM}	Repetitive Peak Reverse Current	T_C= 100℃, V_{RRM} applied		-	-	8.5	mA
T_{rr}	Reverse Recovery Time	I_{FM}= 200A, V_R= 300V di/dt=-100A/us	T_C = 25℃	-	95	100	ns
			T_C = 100℃	-	180	-	ns

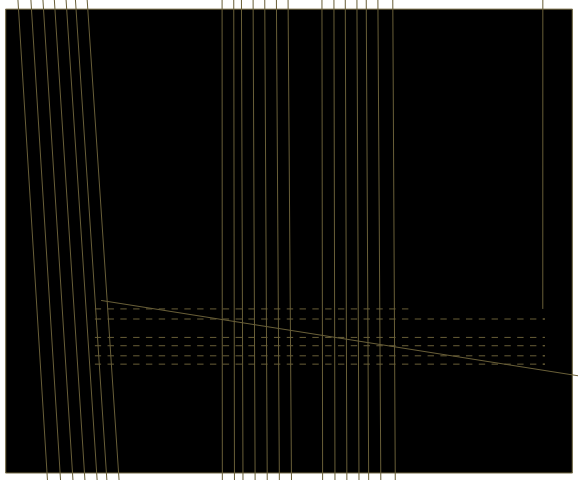


Fig. 2 : Typical Reverse Recovery Time vs. -di/dt